FAIRCHILD SEMICONDUCTOR®

December 2010

FDD850N10L

N-Channel PowerTrench® MOSFET

100V, 15.7A, 75mΩ

Features

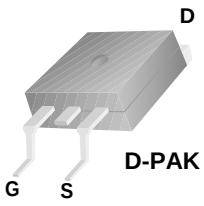
- $R_{DS(on)}$ = 61mΩ (Typ.) @ V_{GS} = 10V, I_D = 12A
- $R_{DS(on)}$ = 64mΩ (Typ.) @ V_{GS} = 5V, I_D = 12A
- Low Gate Charge (Typ. 22.2nC)
- Low C_{rss} (Typ. 42pF)
- Fast Switching
- 100% Avalanche Tested
- Improve dv/dt Capability
- RoHS Compliant

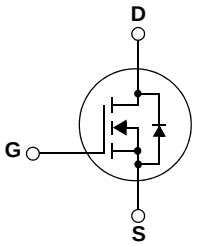
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC to DC Converters / Synchronous Rectification





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol	Parameter		Rating	Units
V_{DSS}	Drain to Source Voltage		100	V
V_{GSS}	Gate to Source Voltage		±20	V
I_D	Drain Current	- Continuous (T_C = 25°C)	15.7	A
		- Continuous (T_C = 100°C)	11.1	
I_{DM}	Drain Current	- Pulsed (Note 1)	63	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	41	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
P_D	Power Dissipation	(T_C = 25°C)	50	W
		- Derate above 25°C	0.33	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Min.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	-	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	87	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD850N10L	FDD850N10L	D-PAK	380mm	16mm	2500

Electrical Characteristics $T_C = 25^oC$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	-	0.1	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 80V, T_C = 150°C	-	-	500	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	1.0	-	2.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 12A	-	61	75	mΩ
		V_{GS} = 5V, I_D = 12A	-	64	96	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 15.7A (Note 4)	-	31	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	-	1100	1465	pF
C_{oss}	Output Capacitance		-	80	105	pF
C_{rss}	Reverse Transfer Capacitance		-	42	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{GS} = 10V, V_{DS} = 80V, I_D = 15.7A	-	22.2	28.9	nC
$Q_{g(tot)}$	Total Gate Charge at 5V	V_{GS} = 5V, V_{DS} = 80V, I_D = 15.7A	-	12.3	16.0	nC
Q_{gs}	Gate to Source Gate Charge	V_{DS} = 80V, I_D = 15.7A	-	3.0	-	nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DS} = 80V, I_D = 15.7A	-	5.7	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50V, I_D = 15.7A, V_{GS} = 5V, R_{GEN} = 4.7Ω (Note 4, 5)	-	17	44	ns
t_r	Turn-On Rise Time		-	21	52	ns
$t_{d(off)}$	Turn-Off Delay Time		-	27	64	ns
t_f	Turn-Off Fall Time		-	8	26	ns
ESR	Equivalent Series Resistance (G-S)		-	1.75	-	Ω
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	15.7	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	63	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 12A	-	-	1.3	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, V_{DS} = 80V, I_{SD} = 15.7A, dI_F/dt = 100A/μs (Note 4)	-	38	-	ns
Q_{rr}	Reverse Recovery Charge		-	50	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 1mH, I_{AS} = 9.1A, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 15.7A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Dual Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

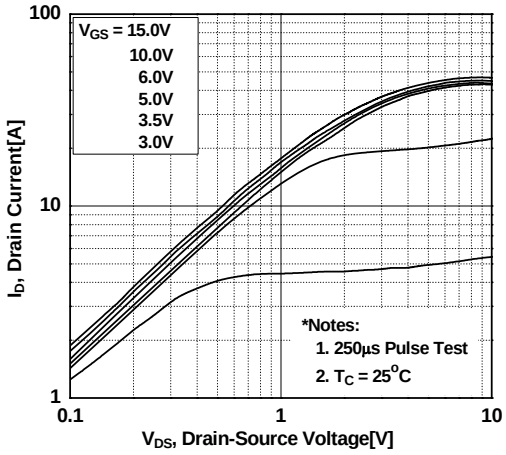


Figure 2. Transfer Characteristics

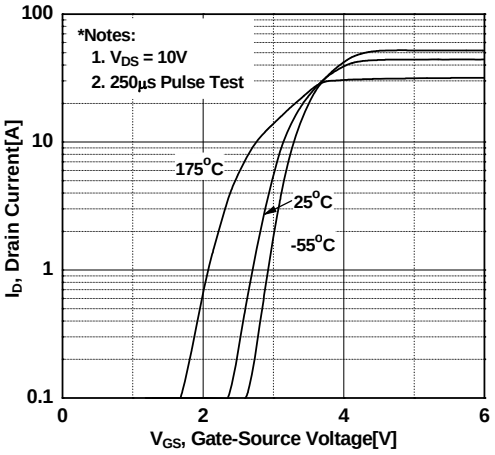


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

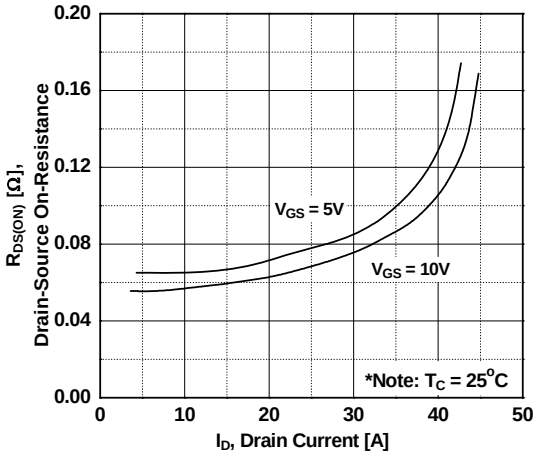


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

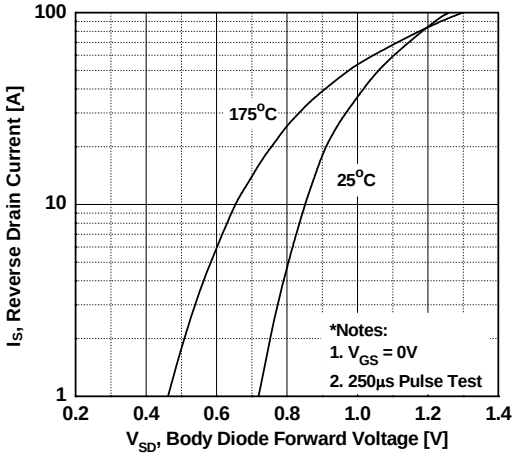


Figure 5. Capacitance Characteristics

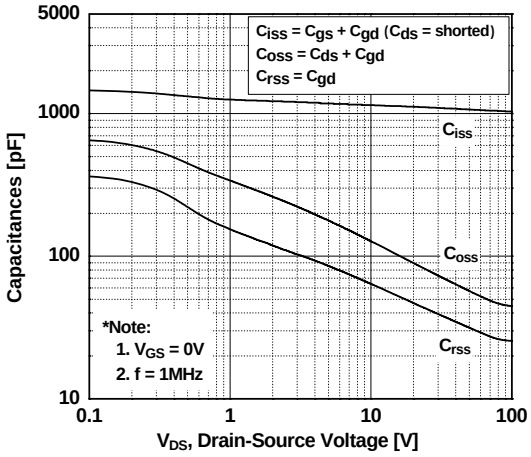
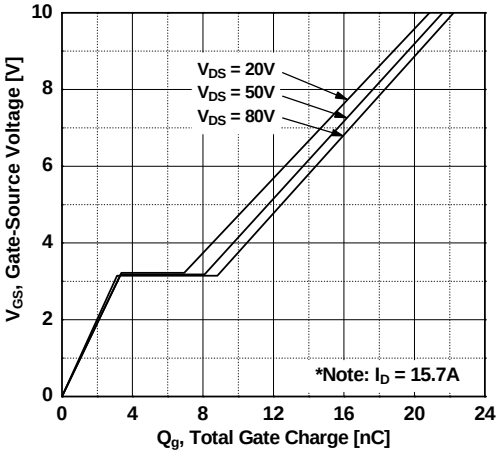


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

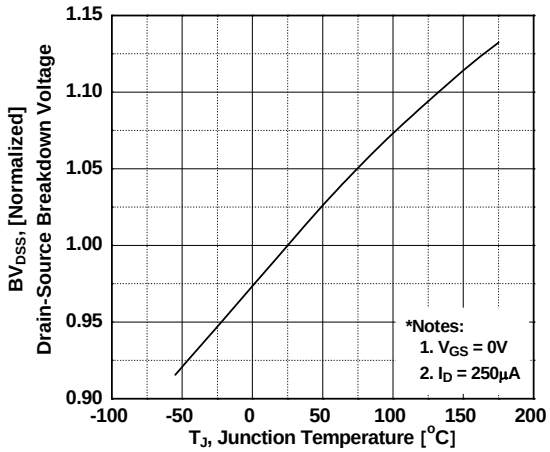


Figure 8. On-Resistance Variation vs. Temperature

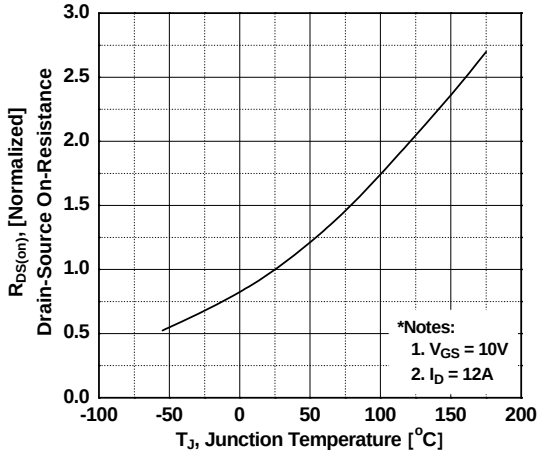


Figure 9. Maximum Safe Operating Area vs. Case Temperature

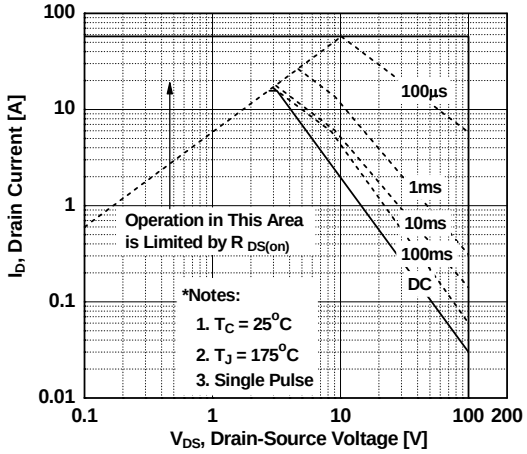


Figure 10. Maximum Drain Current

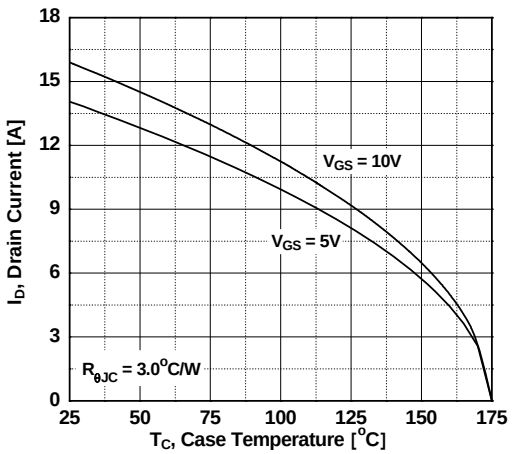
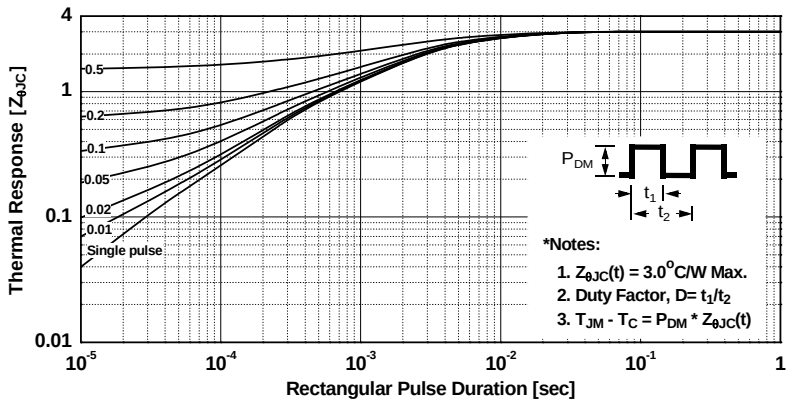
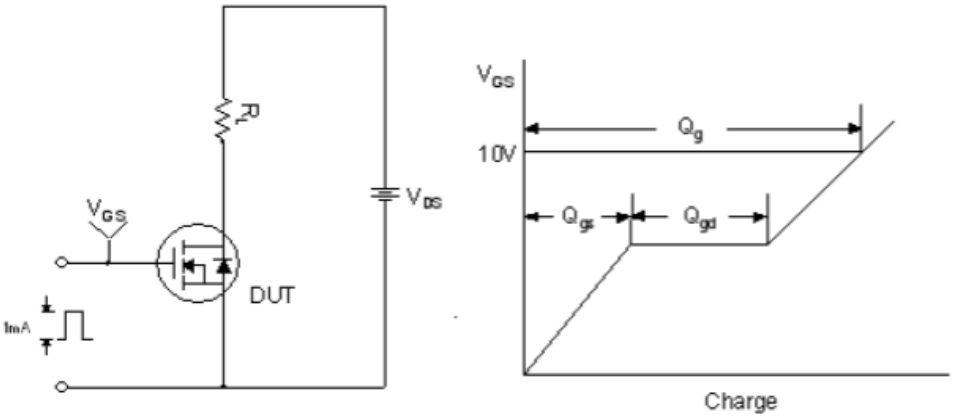


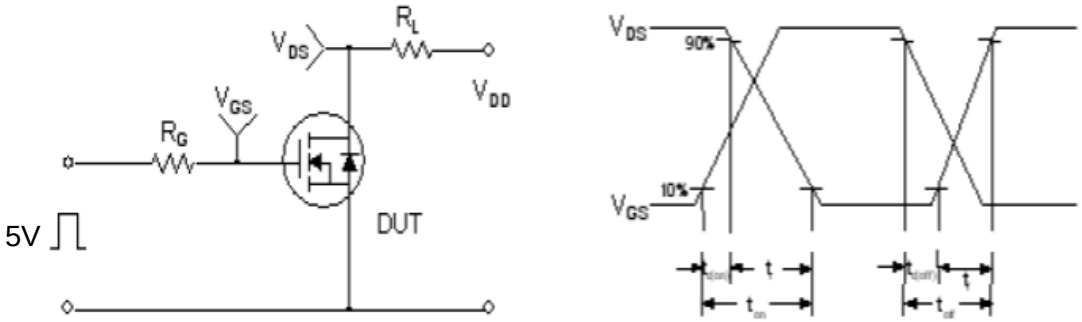
Figure 11. Transient Thermal Response Curve



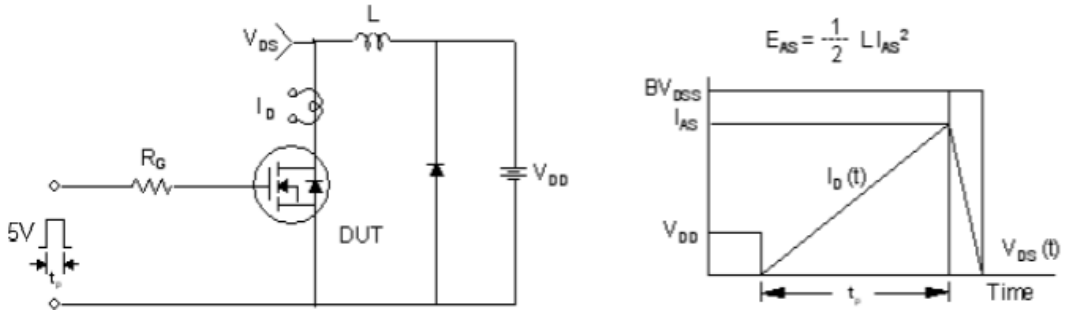
Gate Charge Test Circuit & Waveform



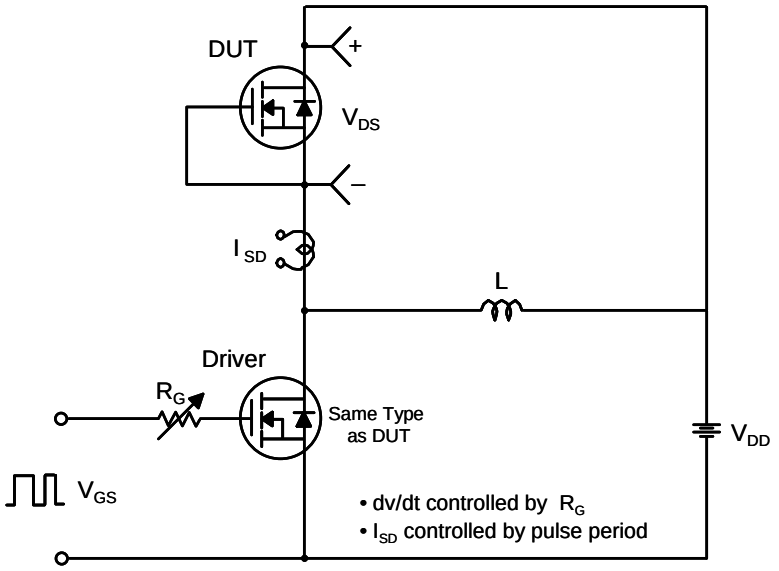
Resistive Switching Test Circuit & Waveforms

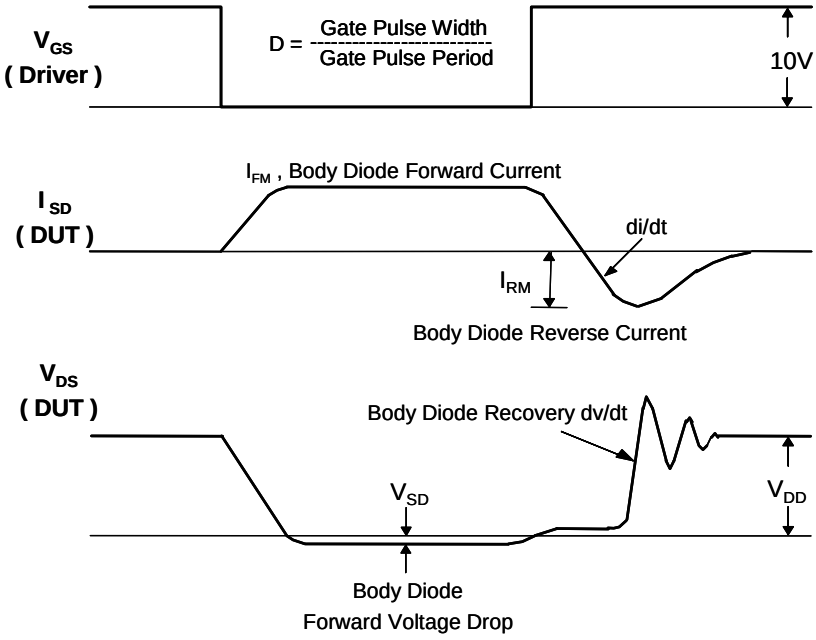


Unclamped Inductive Switching Test Circuit & Waveforms



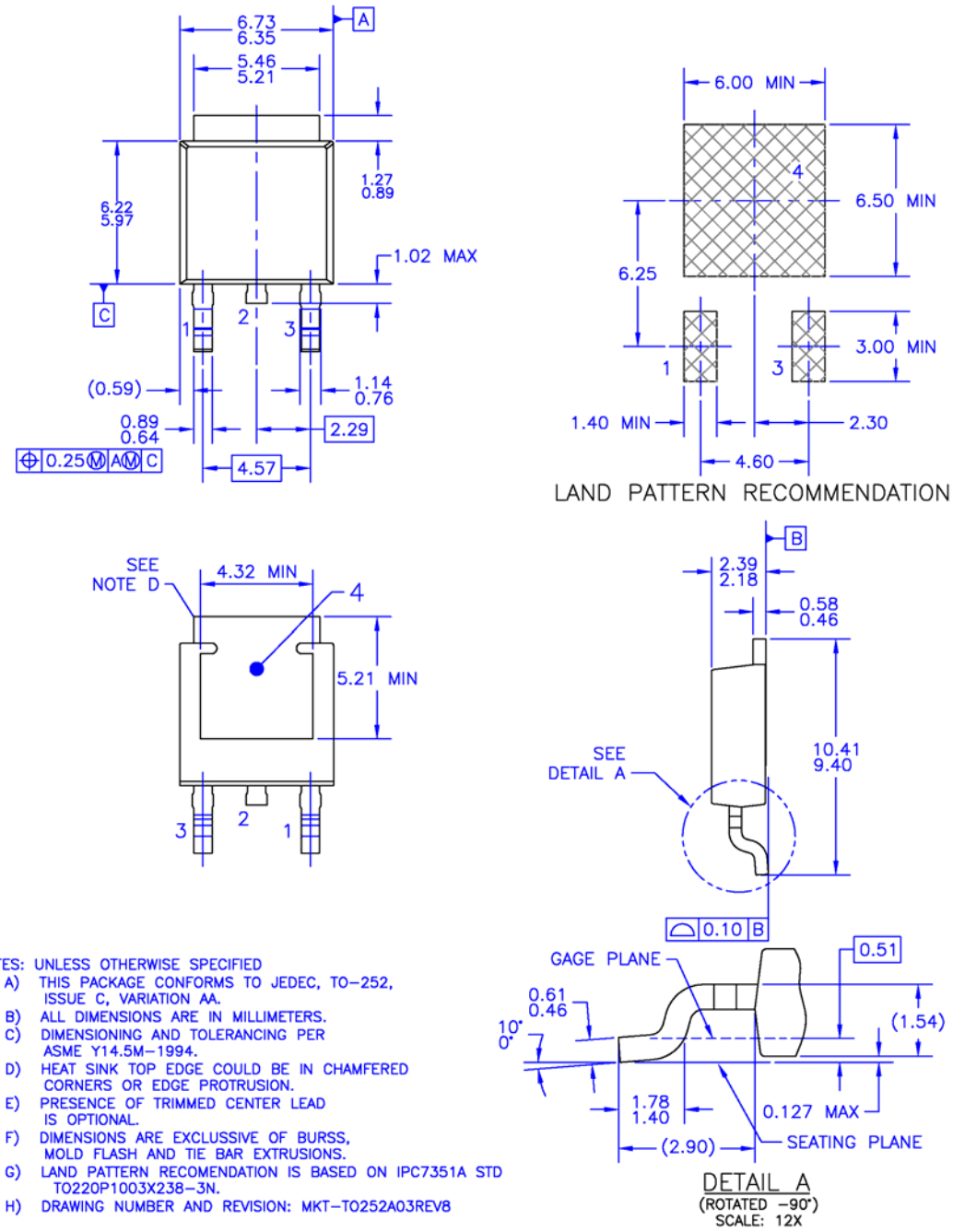
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

D-PAK



NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.
F) DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.
G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO220P1003X238-3N.
H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV8

Dimensions in Millimeters

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